

BT2X32120Q2

1200V Silicon Carbide Diode

Features

- 1200-Volt Schottky Rectifier
- Shorter recovery time
- High-speed switching possible
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

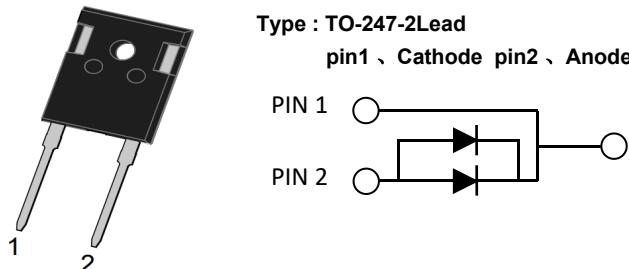
Benefits

- Higher safety margin against overvoltage
- Improved efficiency all load conditions
- Increased efficiency compared to Silicon Diode alternatives
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives
- HID Lighting

Package



Absolute Maximum Ratings

$T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	BT2X32120Q2	Units
VRRM	Repetitive Peak Reverse Voltage	1200	V
VRSM	Surge Peak Reverse Voltage	1200	V
VDC	DC Blocking Voltage	1200	V
IF	Continuous Forward Current @ $T_c=150^\circ\text{C}$	16*2	A
IFRM	Repetitive Peak Forward Surge Current (Per Leg) @ $T_c=25^\circ\text{C}$, tP = 10 ms, Half Sine Wave	80	A
IFSM	Non-Repetitive Peak Forward Surge Current (Per Leg) @ $T_c=25^\circ\text{C}$, tP = 10 ms, Half Sine Wave	120	A
Ptot	Power Dissipation @ $T_c=25^\circ\text{C}$ (Per Leg/Device) @ $T_c=110^\circ\text{C}$	283 122	W
TJ , Tstg	Operating Junction and Storage Temperature	-55 to +175	°C

Electrical Characteristics

T_C = 25° C unless otherwise noted

Symbol	Test Conditions	Test Conditions	Min	Typ	Max	Unit
VF	Forward Voltage(Per Leg)	IF=15A, TC=25° C IF=15A, TC=175° C	-	1.5 2.2	1.8 2.5	V
IR	Reverse Current	VR=1200V, TC=25° C VR=1200V, TC=175° C	-	10 50	100 100	µA
QC	Total Capacitive Charge	VR =800V, TJ = 25° C $Qc = \int_0^{VR} C(V) dv$	-	78	-	nC
C	Total Capacitance	VR =0V, TJ = 25° C, f=1MHz VR =400V, TJ = 25° C, f=1MHz VR =800V, TJ = 25° C, f=1MHz	-	1090 70 53	-	pF
EC	Capacitance Stored Energy	VR=800V	-	40	-	µJ

Thermal Characteristics

Symbol	Parameter	Typ	Unit
R _{θJC}	Thermal Resistance from Junction to Case	0.53	°C/W

Package Marking

Part Number	Top Marking	Package	Packing Method	MOQ	QTY
BT2X32120Q2	BT2X32120Q2	TO-247-2L	Tube	450	2250

Typical Characteristics

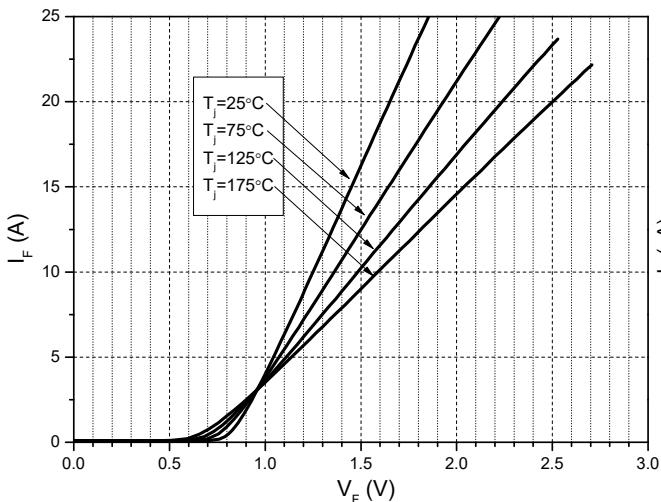


Figure 1. Forward Characteristics

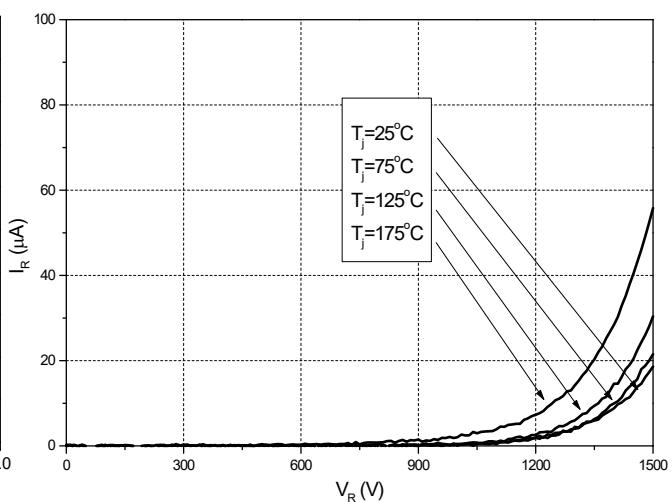


Figure 2. Reverse Characteristics

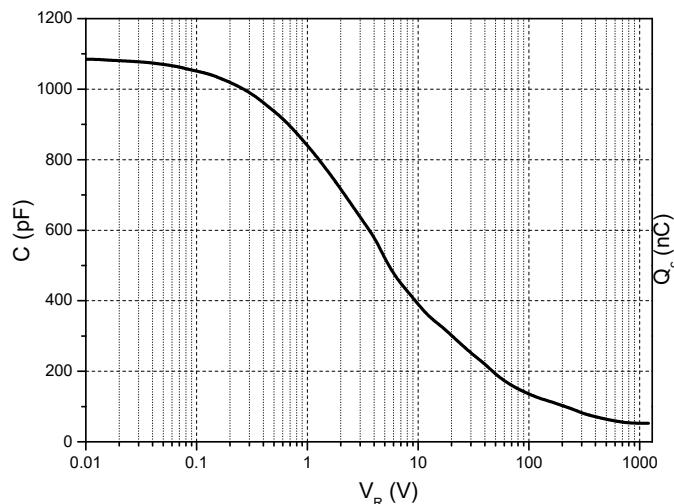


Figure 3. Capacitance vs. Reverse Voltage

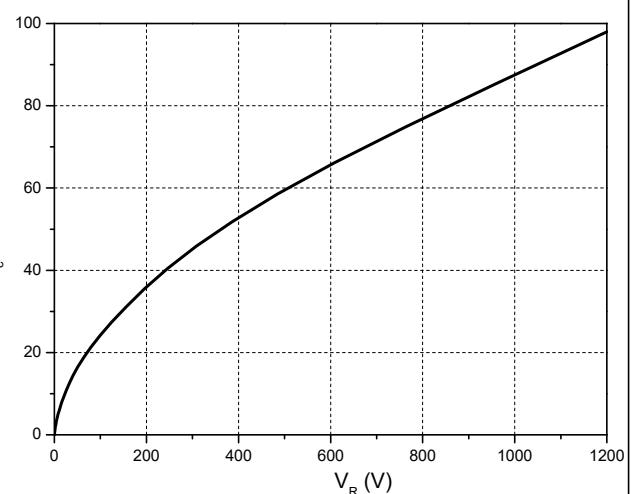


Figure 4. Total Capacitance Charge vs. Reverse Voltage

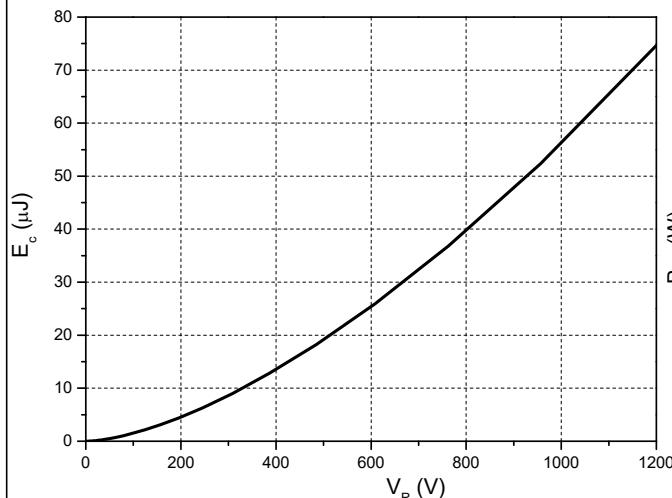


Figure 5. Capacitance Stored Energy

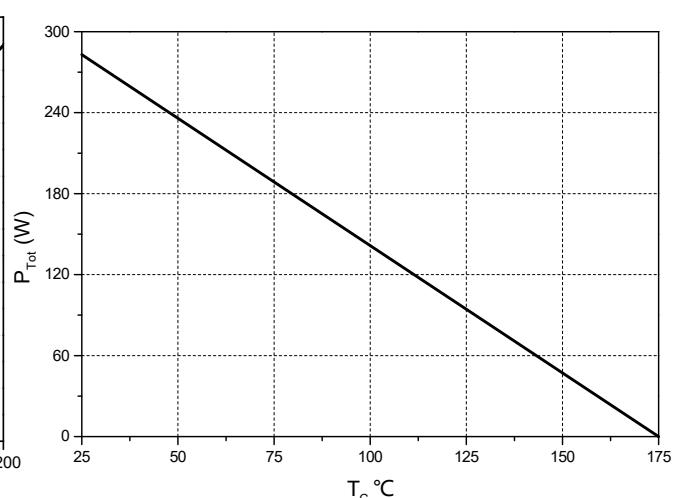


Figure 6. Power Derating

Typical Characteristics

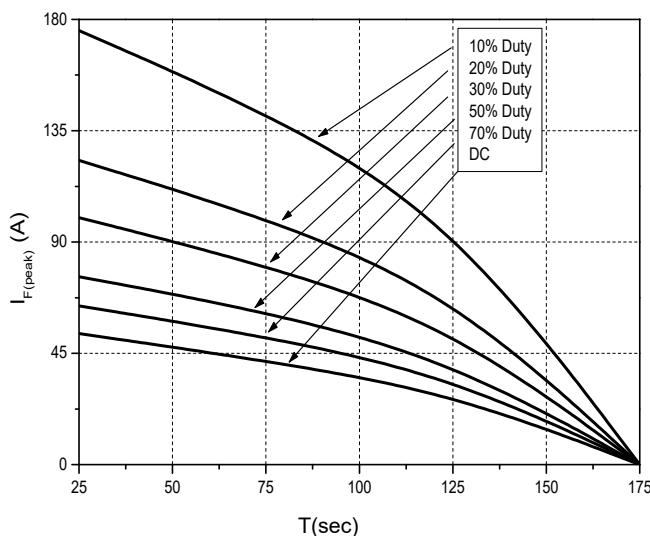


Figure 7. Current Derating

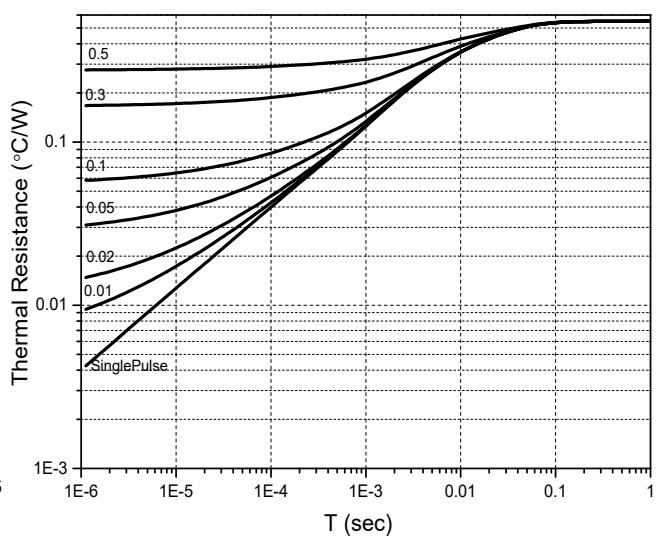
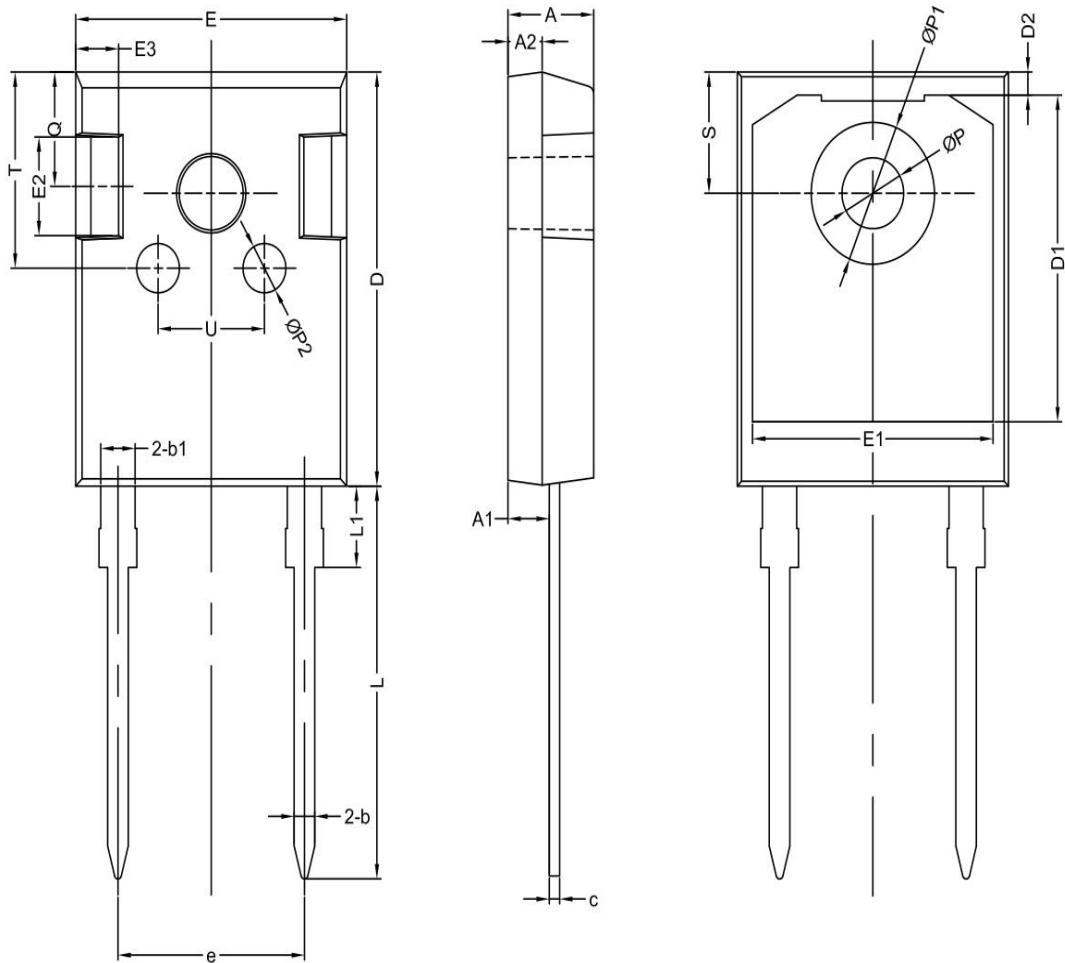


Figure 8. Transient Thermal Impedance



SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm		
	MIN	NOM	MAX						MIN	NOM	MAX
A	4.80	5.00	5.20	D1	-	16.55	-	L1	-	4.13	-
A1	2.21	2.41	2.61	D2	-	1.17	-	Ø P	3.4	3.6	3.8
A2	1.90	2.00	2.10	E	15.50	15.80	16.10	Ø P1	-	7.19	-
b	1.05	1.20	1.35	E1		14.02		Ø P2	-	2.50	-
b1	-	2.00	-	E2		5.0		Q	-	5.8	-
c	0.55	0.60	0.75	e	10.88			S	6.00	6.15	6.25
D	20.65	21.00	21.20	L	19.22	19.92	20.42	T	-	10.0	-

NOTE:

1.The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceRa=0.8

2.Undeclared tolerance ± 0.15 , Unmarked filletRmax=0.25

NAME	TO-247-2L OUTLINE	UNIT	mm	DESIGNED	Shawn	THIRD ANGLE SYSTEM
DWGNO		PAGE	1 OF 1	CHECKED		
VERSION	Ver1.0	ISSUE DATE		APPROVED		